# 2SC2733

## Silicon NPN Epitaxial

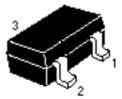
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#### **Application**

VHF frequency converter

#### Outline

MPAK



- 1. Emitter
- 2.Base
- 3. Collector



### 2SC2733

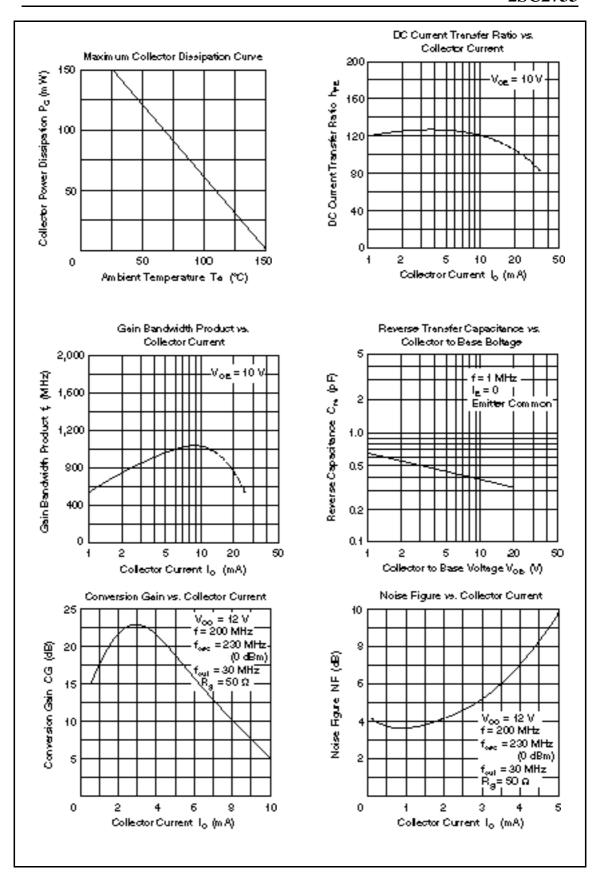
#### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

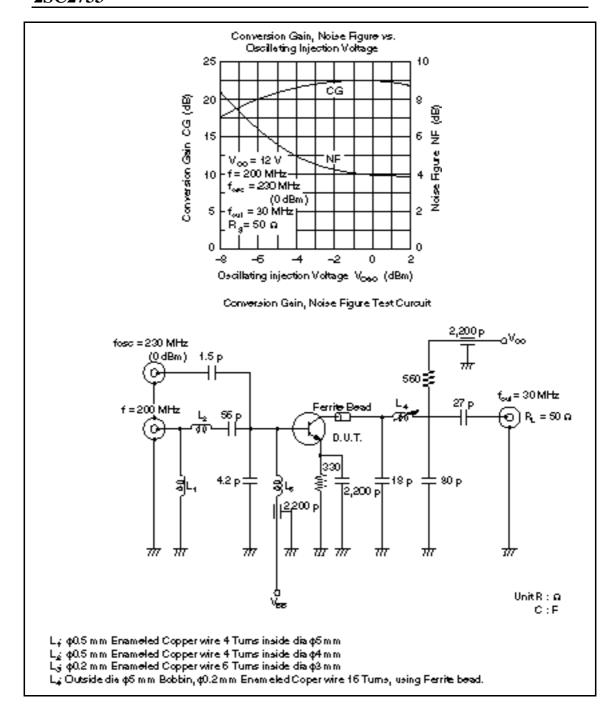
| Item                         | Symbol           | Ratings     | Unit |
|------------------------------|------------------|-------------|------|
| Collector to base voltage    | $V_{\text{CBO}}$ | 30          | V    |
| Collector to emitter voltage | $V_{\text{CEO}}$ | 20          | V    |
| Emitter to base voltage      | $V_{EBO}$        | 3           | V    |
| Collector current            | I <sub>c</sub>   | 50          | mA   |
| Collector power dissipation  | P <sub>c</sub>   | 150         | mW   |
| Junction temperature         | Tj               | 150         | °C   |
| Storage temperature          | Tstg             | -55 to +150 | °C   |

### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

| Item                                    | Symbol               | Min | Тур  | Max  | Unit | Test conditions   |
|---|----------------------|-----|------|------|------|---|
| Collector to base breakdown voltage     | $V_{(BR)CBO}$        | 30  | _    | _    | V    | $I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$   |
| Collector to emitter breakdown voltage  | $V_{(BR)CEO}$        | 20  | _    | _    | V    | $I_c = 1 \text{ mA}, R_{BE} =$  |
| Emitter to base breakdown voltage       | $V_{(BR)EBO}$        | 3   | _    | _    | V    | $I_{E} = 10 \ \mu A, \ I_{E} = 0$   |
| Collector cutoff current                | I <sub>CBO</sub>     | _   | _    | 0.5  | μΑ   | $V_{CB} = 10 \text{ V}, I_{C} = 0$  |
| Collector to emitter saturation voltage | $V_{\text{CE(sat)}}$ | _   | _    | 1.0  | V    | $I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 4 mA   |
| DC current transfer ratio               | $h_{FE}$             | 60  | 120  | _    |      | $V_{CE}$ = 10 V, $I_{C}$ = 10 mA  |
| Gain bandwidth product                  | f <sub>T</sub>       | 600 | 1000 | _    | MHz  | $V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$  |
| Collector output capacitance            | Cob                  | _   | 0.35 | 0.65 | pF   | $V_{CB} = 10 \text{ V}$ , Emitter ground, $f = 1 \text{ MHz}$   |
| Conversion gain                         | CG                   | _   | 21   | _    | dB   | $V_{CC}$ = 12 V, $I_{C}$ = 2 mA,<br>f = 200 MHz,<br>$f_{OSC}$ = 230 MHz (0dBm),<br>$f_{out}$ = 30 MHz |
| Noise figure                            | NF                   | _   | 4.0  | _    | dB   | $V_{CC}$ = 12 V, $I_{C}$ = 2 mA,<br>f = 200 MHz,<br>$f_{OSC}$ = 230 MHz (0dBm),<br>$f_{out}$ = 30 MHz |

Note: Marking is "HC".





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